WNSC6D10650T

Silicon Carbide Diode

Rev.02 - 27 April 2023

Product data sheet

1. General description

Silicon Carbide Schottky diode in a DFN 8*8 plastic package, designed for high frequency switched-mode power supplies.

2. Features and benefits

- New 6th Generation Technology
- Low Forward Voltage Drop
- Low Reverse Leakage Current
- High Forward Surge Capability I_{FSM}
- Reduced losses in associated MOSFET
- Reduced EMI
- Reduced cooling requirements
- RoHS compliant

3. Applications

- Power factor correction
- Telecom / Server SMPS
- UPS
- PV inverter
- PC Silverbox
- LED / OLED TV
- Motor Drives

4. Quick reference data

Table 1. Q	uick reference data						
Symbol	Parameter	Conditions	Notes	Values			Unit
Absolute	maximum rating						
V_{RRM}	repetitive peak reverse voltage				650		V
$I_{F(AV)}$	average forward current	δ = 0.5 ; square-wave pulse; T _c ≤ 153 °C; <u>Fig. 1; Fig. 2; Fig. 3</u>			10		A
T _j	junction temperature			-55 to 175		°C	
Symbol	Parameter	Conditions	Notes	Min	Тур	Max	Unit
Static ch	aracteristics						
V _F	forward voltage	I _F = 10 A; T _j = 25 °C; <u>Fig. 5</u>		-	1.29	1.45	V
		I _F = 10 A; T _j = 150 °C; <u>Fig. 5</u>		-	1.45	1.65	V
Dynamic	characteristics		1			1	
Q _r	recovered charge	I _F = 10 A; dI _F /dt = 500 A/μs; V _R = 400 V; T _j = 25 °C; <u>Fig. 7</u>		-	24	-	nC





5. Pinning information

Pin	Symbol	Description	Simplified outline	Graphic symbol
1	n.c.	not connected	[]	к-Ң-А
2	n.c.	not connected	5	001aaa020
3	А	anode		
4	А	anode		
5	К	mounting base; connected to cathode	1 2 3 4	

6. Ordering information

Table 3. Ordering information								
Type number	Package	Orderable part number	Packing	Small packing	Package	Package		
	name		method	quantity	version	issue date		
WNSC6D10650T	DFN8*8	WNSC6D10650T6J	Таре	3000	DFN8X8N	25-Dec-2019		

7. Marking

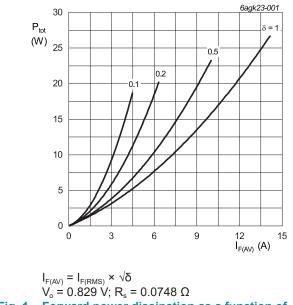
Table 4. Marking codes						
Type number	Marking codes					
WNSC6D10650T	WNSC6D					
	10650T					

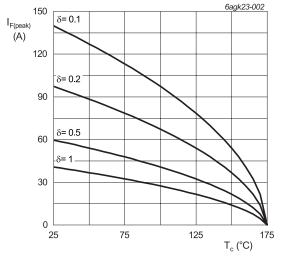
8. Limiting values

Table 5. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions	Notes	Values	Unit
V_{RRM}	repetitive peak reverse voltage			650	V
V_{RWM}	crest working reverse voltage			650	V
V _R	reverse voltage	DC		650	V
I _{F(AV)}	average forward current	δ = 0.5; square-wave pulse; T _c ≤ 153 °C; Fig. 1; Fig. 2; Fig. 3		10	A
I _{FRM}	repetitive peak forward current	δ = 0.5; t _p = 25 μs; T _c ≤ 153 °C; square-wave pulse		20	A
I _{FSM}	non-repetitive peak	t_p = 10 ms; $T_{j(init)}$ = 25 °C; sine-wave pulse		75	А
	forward current	$t_p = 10 \ \mu s; T_{j(init)} = 25 \ ^{\circ}C; square-wave pulse$		800	А
l ² t	l ² t for fusing	sine-wave pulse; $T_{j(init)}$ = 25 °C; t_p = 10 ms		28.125	A ² s
T _{stg}	storage temperature			-55 to 175	°C
T _j	junction temperature			-55 to 175	°C

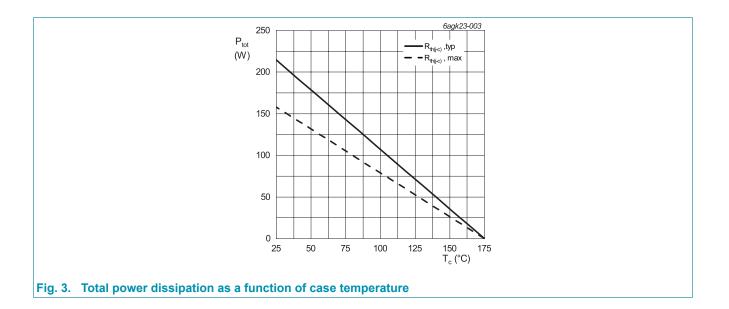






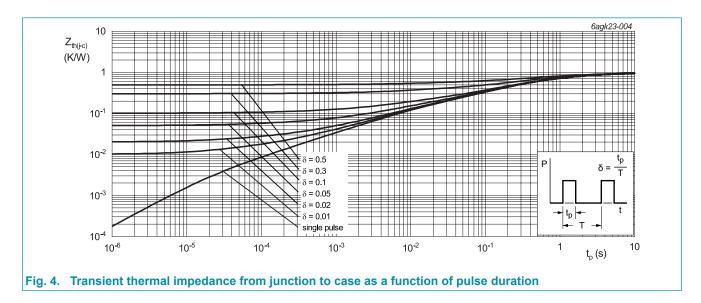
	$V_{o} = 0.829 \text{ V}; \text{ R}_{s} = 0.0748 \Omega$
Fig. 1.	Forward power dissipation as a function of
	average forward current; square waveform;
	maximum values

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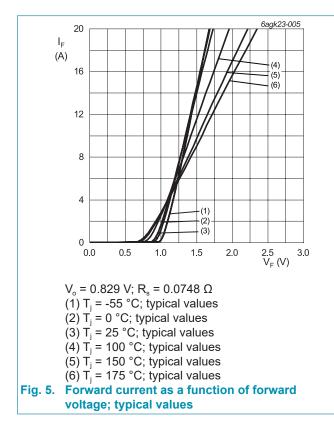
9. Thermal characteristics

Table 6. Th	ermal characteristics						
Symbol	Parameter	Conditions	Notes	Min	Тур	Max	Unit
R _{th(j-c)}	thermal resistance from junction to case	<u>Fig. 4</u>		-	0.7	0.95	K/W
$R_{th(j-a)}$	thermal resistance from junction to ambient free air	in free air		-	60	-	K/W



10. Characteristics

Symbol	Parameter	Conditions	Notes	Min	Тур	Max	Unit
Static cha	aracteristics				_	_	
V _F	forward current	I _F = 10 A; T _j = 25 °C; <u>Fig. 5</u>		-	1.29	1.45	V
		I _F = 10 A; T _j = 150 °C; <u>Fig. 5</u>		-	1.45	1.65	V
		I _F = 10 A; T _j = 175 °C; <u>Fig. 5</u>		-	1.50	1.70	V
I _R	reverse current	V _R = 650 V; T _j = 25 °C; <u>Fig. 6</u>		-	1	50	μA
		V _R = 650 V; T _j = 175 °C; <u>Fig. 6</u>		-	15	200	μA
Dynamic	characteristics	-					-
Q _r	recovered charge	$I_F = 10 \text{ A}; V_R = 400 \text{ V}; \text{ d}_F/\text{d}t = 500 \text{ A}/\mu\text{s};$ $T_j = 25 \text{ °C}; Fig. 7$		-	24	-	nC
C _d	diode capacitance	f = 1 MHz; V _R = 1 V; T _j = 25 °C		-	500	-	pF
		f = 1 MHz; V _R = 300 V; T _j = 25 °C		-	58	-	pF
		f = 1 MHz; V _R = 600 V; T _j = 25 °C		-	52	-	pF
E _{as}	non-repetitive avalanche energy	I _R = 5 A; L = 5 mH; T _{j(init)} = 25 °C		60	-	-	mJ



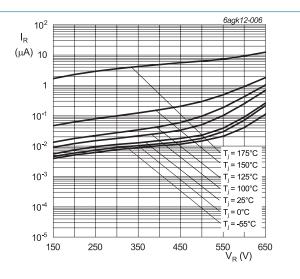
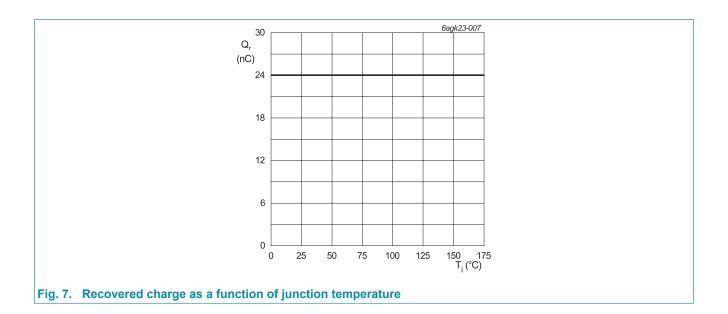
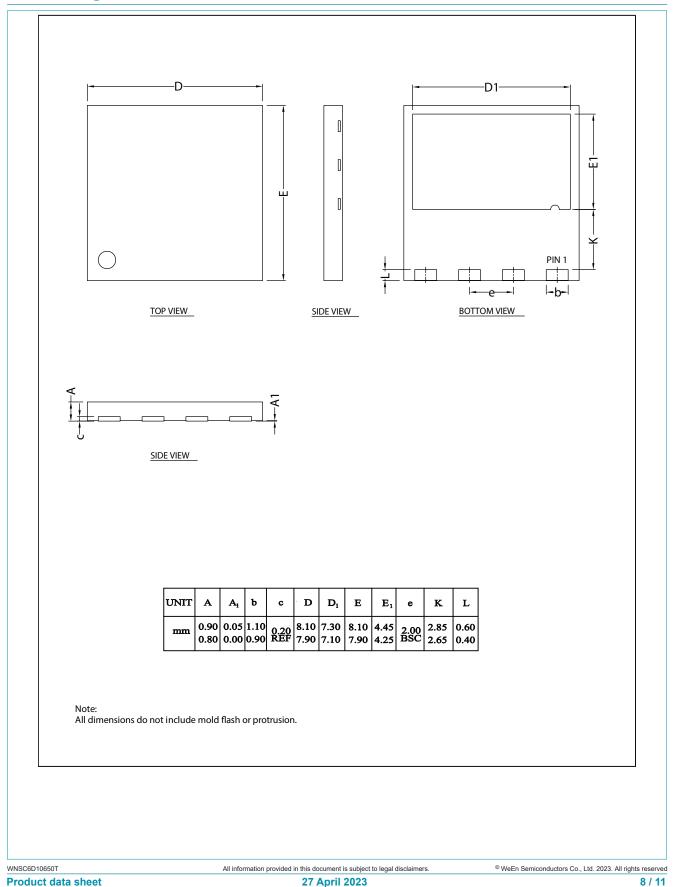


Fig. 6. Reverse leakage current as a function of reverse voltage; typical value

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11. Package outline



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12. Legal information

Data sheet status

Document status [1][2]	Product status [3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

[1] Please consult the most recently issued document before initiating or completing a design.

- [2] The term 'short data sheet' is explained in section "Definitions".
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